

Switching Diode

BAS16L

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	100	V
Peak Forward Current	I_F	200	mA
Non-Repetitive Peak Forward Surge Current 60 Hz	$I_{FSM(surge)}$	1.8	A
Repetitive Peak Forward Current (Note 3)	I_{FRM}	1.0	A
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^\circ\text{C}$ prior to surge) $t = 1\ \mu\text{s}$ $t = 10\ \mu\text{s}$ $t = 100\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 10\ \text{ms}$ $t = 100\ \text{ms}$ $t = 1\ \text{s}$	I_{FSM}	36.0 18.0 6.0 3.0 1.8 1.3 1.0	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

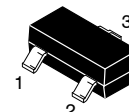
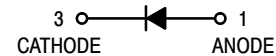
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
3. Square Wave, $f = 40\ \text{kHz}$, $PW = 200\ \text{ns}$
Test Duration = 60 s, $T_J = 25^\circ\text{C}$ prior to surge.



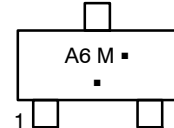
ON Semiconductor®

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SOT-23
CASE 318
STYLE 8

MARKING DIAGRAM



A6 = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAS16LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAS16LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel
SBAS16LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
SBAS16LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel

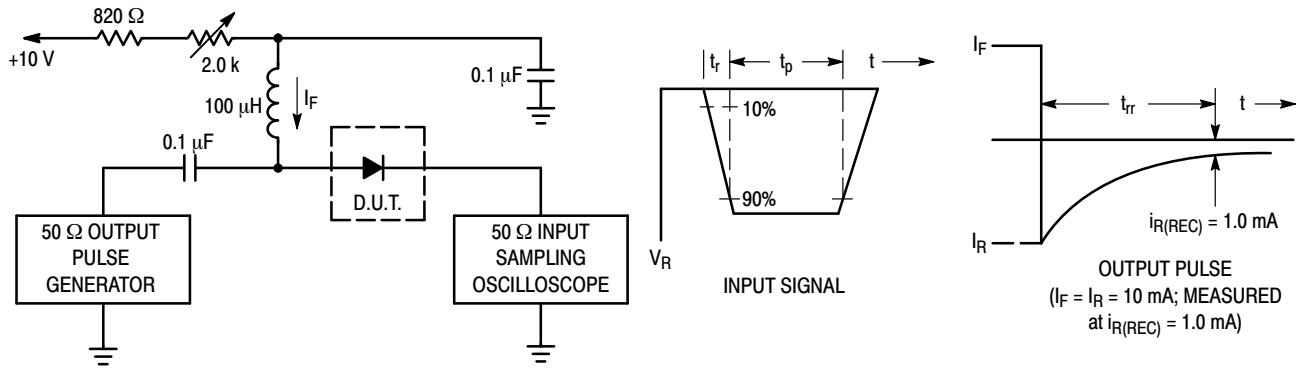
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current ($V_R = 100\text{ V}$) ($V_R = 75\text{ Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 25\text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_R	–	1.0 50 30	μAdc
Reverse Breakdown Voltage ($I_{BR} = 100\text{ }\mu\text{Adc}$)	$V_{(BR)}$	100	–	Vdc
Forward Voltage ($I_F = 1.0\text{ mAdc}$) ($I_F = 10\text{ mAdc}$) ($I_F = 50\text{ mAdc}$) ($I_F = 150\text{ mAdc}$)	V_F	–	715 855 1000 1250	mV
Diode Capacitance ($V_R = 0$, $f = 1.0\text{ MHz}$)	C_D	–	2.0	pF
Forward Recovery Voltage ($I_F = 10\text{ mAdc}$, $t_r = 20\text{ ns}$)	V_{FR}	–	1.75	Vdc
Reverse Recovery Time ($I_F = I_R = 10\text{ mAdc}$, $R_L = 50\text{ }\Omega$)	t_{rr}	–	6.0	ns
Stored Charge ($I_F = 10\text{ mAdc}$ to $V_R = 5.0\text{ Vdc}$, $R_L = 500\text{ }\Omega$)	Q_S	–	45	pC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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TYPICAL CHARACTERISTICS

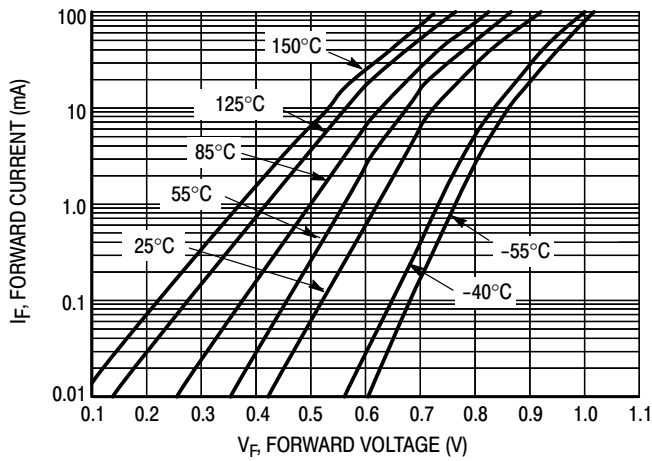


Figure 2. V_F vs. I_F

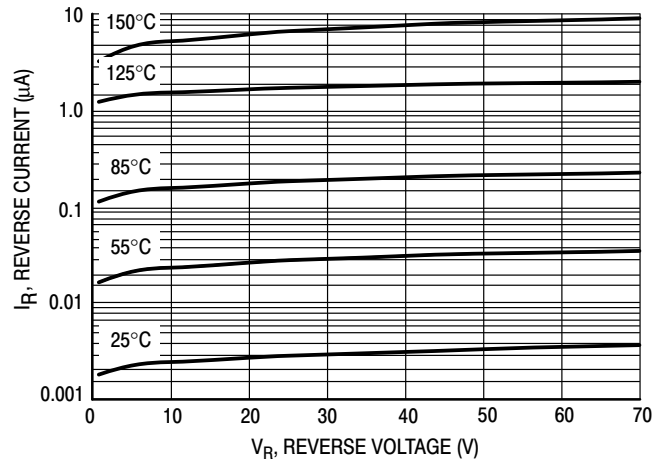


Figure 3. I_R vs. V_R

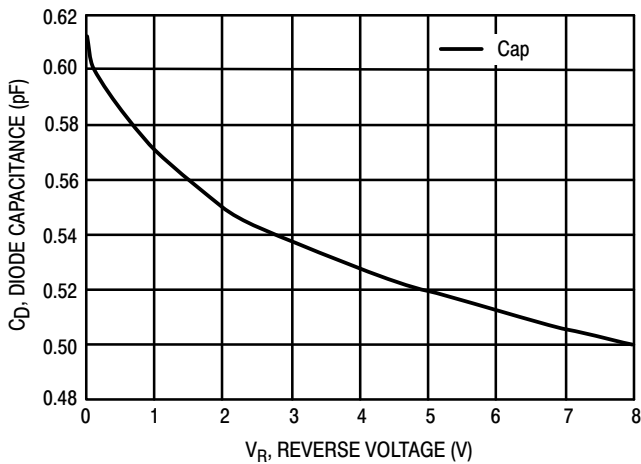


Figure 4. Capacitance

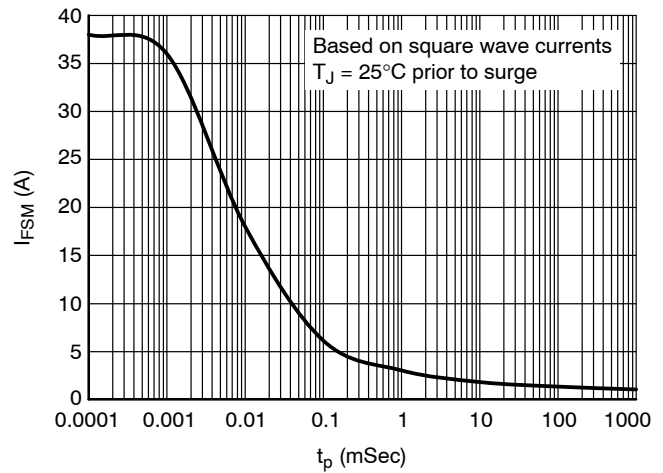


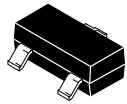
Figure 5. Maximum Non-repetitive Peak Forward Current as a Function of Pulse Duration, Typical Values

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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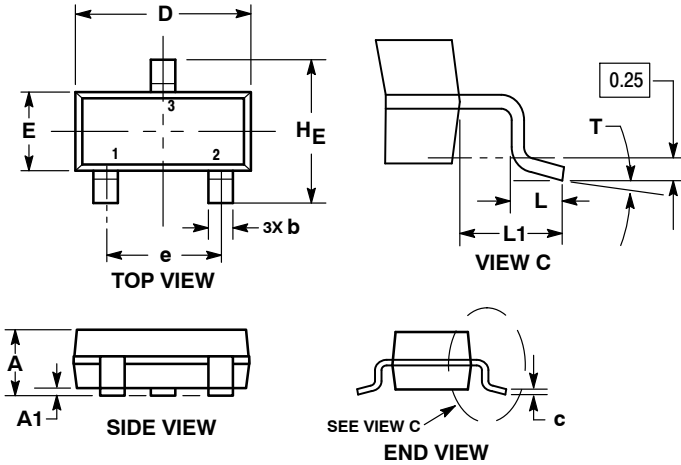
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SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

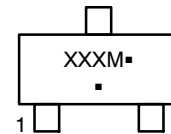


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

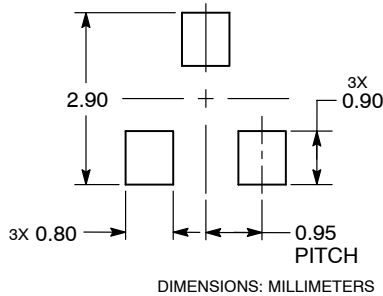
GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT



STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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